

AMENDMENTS TO THE CLAIMS:

Please cancel claim 12 without prejudice, amend claims 10 and 14, and add new claims 23 and 24. This listing of claims will replace all prior versions and listings of claims in the application:

1. (Withdrawn) A semiconductor device, comprising:
a gate oxide located over a substrate; and
a silicided gate electrode located over said gate oxide, said silicided gate electrode including a first metal and a second metal.
2. (Withdrawn) The semiconductor device as recited in claim 1 further including a dopant located within and configured to tune a work function of said silicided gate electrode.
3. (Withdrawn) The semiconductor device as recited in claim 2 wherein said dopant is selected from a group consisting of:
boron;
phosphorous; and
arsenic.
4. (Withdrawn) The semiconductor device as recited in claim 1 further including source/drain regions located in said substrate proximate said gate oxide and silicided source/drain contact regions located in said source/drain regions, wherein said silicided

source/drain contact regions have a depth substantially different than a thickness of said silicided gate electrode.

5. (Withdrawn) The semiconductor device as recited in claim 4 wherein said silicided gate electrode is silicided with a different metal than said silicided source/drain contact regions.

6. (Withdrawn) The semiconductor device as recited in claim 1 wherein said first metal is cobalt and said second metal is nickel.

7. (Withdrawn) The semiconductor device as recited in claim 6 wherein a ratio of an atomic percent of said cobalt to said nickel in said silicided gate electrode ranges from about 9:1 to about 2:3.

8. (Withdrawn) The semiconductor device as recited in claim 7 wherein said atomic percent ranges from about 3:1 to about 1:1.

9. (Withdrawn) The semiconductor device as recited in claim 1 wherein said silicided gate electrode has a thickness ranging from about 15 nm to about 150 nm.

10. (Currently Amended) A method for manufacturing a semiconductor device, comprising:

placing a layer of gate oxide material over a substrate; and

forming a layer of silicided gate electrode material over said gate oxide,
comprising: including;
forming a layer of polysilicon material over said blanket layer of gate oxide
material[[:]];
forming a layer of an alloy comprising a first metal and a second metal
over said layer of polysilicon material[[:]];
~~implanting a dopant into said layer of polysilicon material affecting a work-~~
~~function of said silicided gate electrode; and~~
annealing said blanket layer of said alloy comprising said first metal and
said second metal to form a blanket layer of silicided gate electrode material including
said first metal and said second metal; and
patterning said layer of silicided gate electrode material to form a silicided gate
electrode.

11. – 13. (Canceled)

14. (Currently Amended) The method as recited in claim 10 23 further including
forming a capping layer over said layer of said alloy, said capping layer configured to
affect a doping profile of said dopant.

15. (Original) The method as recited in claim 14 wherein said capping layer
comprises a transition metal-nitride.

16. (Canceled)

17. (Withdrawn) The method as recited in claim 11 wherein said cobalt-nickel alloy has a Co.sub.x to Ni.sub.y ratio (x:y) ranging from about 9:1 to about 2:3.

18. (Previously Presented) The method as recited in claim 10 wherein a ratio of an atomic percent of said first metal to said second metal in said silicided gate electrode ranges from about 9:1 to about 2:3.

19. (Original) The method as recited in claim 10 further including forming source/drain regions in said substrate and forming silicided source/drain contact regions in said source/drain regions subsequent to forming said silicided gate electrode.

20. (Withdrawn) An integrated circuit, comprising:

transistors located over a substrate, said transistors including;

a gate oxide located over said substrate;

a silicided gate electrode located over said gate oxide, said silicided gate electrode including a first metal and a second metal; and

an interlevel dielectric layer located over said substrate, said interlevel dielectric layer having interconnects located therein for contacting said transistors.

21. (Previously Presented) The method as recited in claim 18 wherein said first metal is cobalt and said second metal is nickel.

22. (Previously Presented) The method as recited in claim 10 wherein said first metal is cobalt and said second metal is nickel.

23. (New) The method of claim 10, further comprising:
implanting a dopant into said layer of polysilicon material affecting a work function of said silicided gate electrode.

24. (New) The method of claim 10, wherein a ratio of a thickness of the layer of polysilicon material to a thickness of the layer of the alloy is at least approximately 3.6:1.